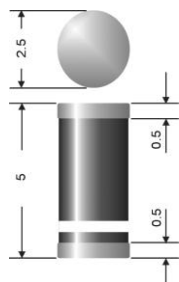


SUF 4001 ... SUF 4007-1200



Surface mount diode

Ultrafast silicon rectifier diodes

SUF 4001 ... SUF 4007

Forward Current: 1 A

Reverse Voltage: 50 to 1200 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case Melf / DO-213AB
- Weight approx.: 0,12 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 5000 pieces per reel

1) Max. temperature of the terminals $T_T = 50^\circ\text{C}$

2) $I_F = 1\text{ A}$, $T_j = 25^\circ\text{C}$

3) $T_A = 25^\circ\text{C}$

4) Mounted on P.C. board with 25 mm² copper pads at each terminal

Type	Polarity color band	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Maximum forward voltage $T_j = 25^\circ\text{C}$ $I_F = 1\text{ A}$ $V_F^{(2)}$ V	Maximum reverse recovery time $I_F = 0,5\text{ A}$ $I_R = 1\text{ A}$ $I_{RR} = 0,25\text{ A}$ t_{rr} ns
SUF 4001	-	50	50	1	50
SUF 4002	-	100	100	1	50
SUF 4003	-	200	200	1	50
SUF 4004	-	400	400	1,25	50
SUF 4005	-	600	600	1,7	75
SUF 4006	-	800	800	1,7	75
SUF 4007	-	1000	1000	1,7	75
SUF 4007-1200		1200	1200	1,7	75

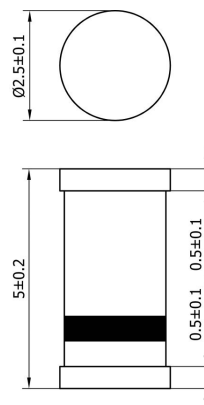
Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_T = 50^\circ\text{C}$	1	A
I_{FRM}	Repetitive peak forward current $f > 15\text{ Hz}^1)$	10	A
I_{FSM}	Peak fwd. surge current 50 Hz half sinus-wave ³⁾	27	A
I^2t	Rating for fusing, $t < 10\text{ ms}^3)$	3,6	A ² s
R_{thA}	Max. thermal resistance junction to ambient ⁴⁾	45	K/W
R_{thT}	Max. thermal resistance junction to terminals	10	K/W
T_j	Operating junction temperature	- 50 ... + 175	°C
T_s	Storage temperature	- 50 ... + 175	°C

Characteristics $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25^\circ\text{C}$; $V_R = V_{RRM}$ $T_j = 100^\circ\text{C}$; $V_R = V_{RRM}$	<10 <50	μA μA
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/ms$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($L = \text{mH}$; $T_j = ^\circ\text{C}$; inductive load switched off)	-	mJ

Dimensions in mm



case: Melf / DO-213AB

